

### : 95HIF9'

- Š [ , ÁZ^ } ^!ÁQ { ] ^áæ } & ^Á
- G€€ { Y ÁÚ [ , ^!ÁÖ!••! ] æcá [ ] Á
- ÁP! \* @ÁÚcæà!j!c^ Áæ } á!P! \* @ÁÚ^!jæà!j!c^

### A97 < 5B=75 @ 85H5

Ôæ•^KØ|æc!Š^æá!ÚUÖEHGHÁÚ { æ||!ÁU^c|! } ^!ÁÚ|æ•c!ÁÚæ&\æ\*^  
Ú [ |æ!æ^K Ô [ | [ | : àæ } á á^ } [ c^• &æc@ [ á^ ^ } á  
T [ ~ } c! } \* Ú [ •!cá [ ] KCE ) ^

### A5L=A I A F5H=B ; G 5B8 7 < 5F57H9F=GH=7G

Üæcá } \* • æc G Í Ô æ { à!á^ } c c^ { ] ^!æc^!^ ~ } | ^•• [ c@^! , !•^ • ] ^&!-!á!á

Parameters	Symbol	Value	Unit
Power Dissipation	Pd	200 <sup>1)</sup>	mW
Forward Voltage @IF=10mA	Vf	0.9	V
Storage temperature range	Ts	-65-+150	

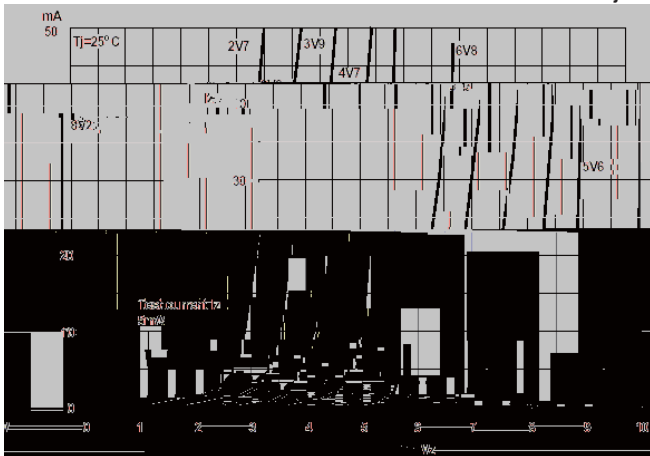
Ç VæMGÍ ~ } | ^•• [ c@^! , !•^ • ] ^&!-!á!áD

Notes: 1. Device mounted on ceramic PCB( 7.6mm x 9.4mm x 0.87mm with pad areas 25mm<sup>2</sup> ·  
2. Short duration test pulse used to minimize self-heating effect.  
3. f = 1kHz.

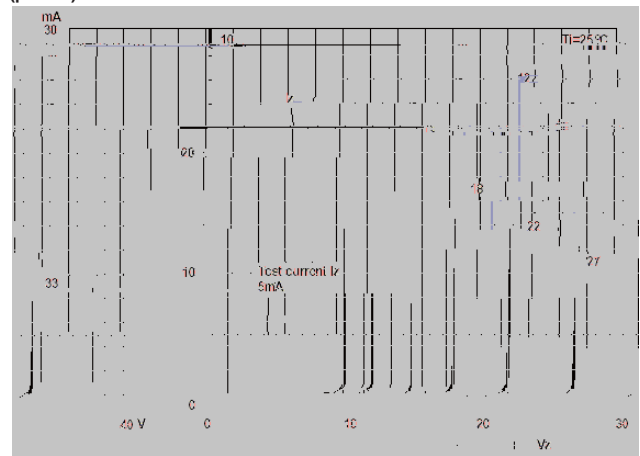
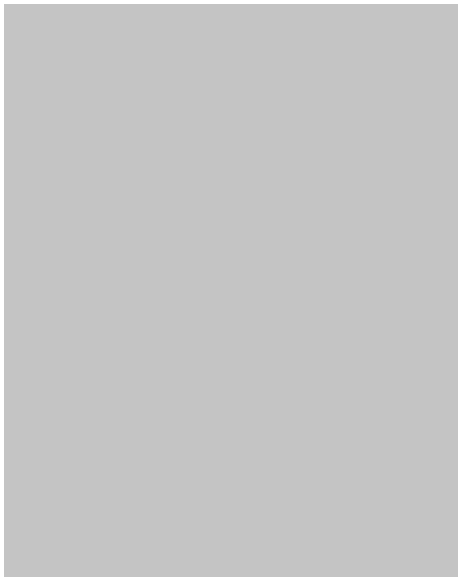
# BZT52B2V4S~BZT52B43S

Device	Marking	Zener Voltage Range				Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/		Test Current IZTC mA
		Vz@Izt			Izt mA	Zzt @Izt	Zzk @Izk	Izk mA	IR uA	VR V	Min	Max	
		Nom(V)	Min(V)	Max(V)									
BZT52B15S	2WJ	15	14.70	15.30	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52B16S	2WK	16	15.68	16.32	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52B18S	2WL	18	17.64	18.36	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52B20S	2WM	20	19.60	20.40	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52B22S	2WN	22	21.56	22.44	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52B24S	2WO	24	23.52	24.48	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52B27S	2WP	27	26.46	27.54	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52B30S	2WQ	30	29.40	30.60	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52B33S	2WR	33	32.34	33.66	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52B36S	2WS	36	35.28	36.72	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52B39S	2WT	39	38.22	39.78	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52B43S	2WU	43	41.16	43.84	2	100	700	1.0	0.1	32.0	10.0	12.0	5

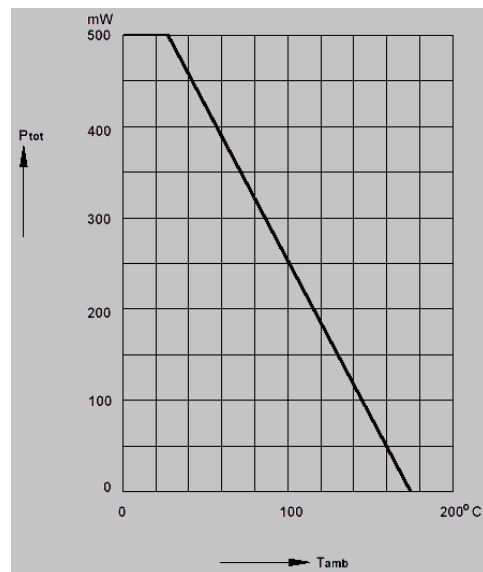
## Breakdown characteristics at $T_j = \text{constant}$ (pulsed)



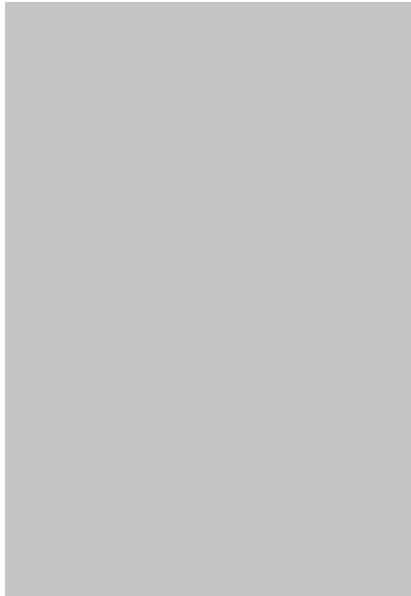
Forward characteristics



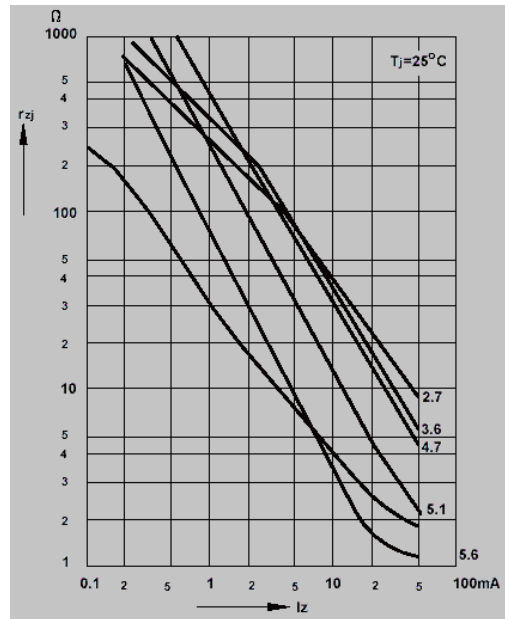
Admissible power dissipation versus ambient temperature



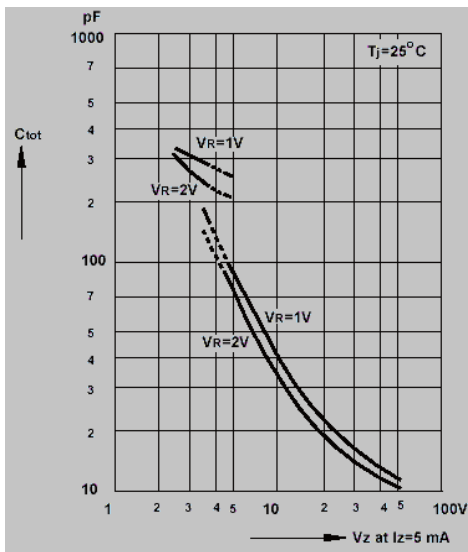
Pulse thermal resistance versus pulse duration



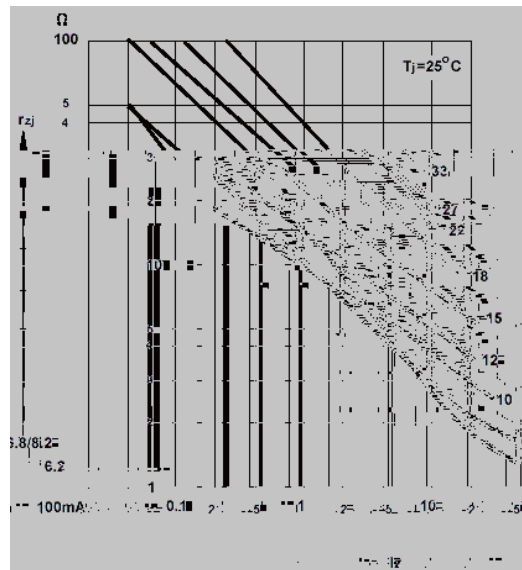
Dynamic resistance versus Zener current



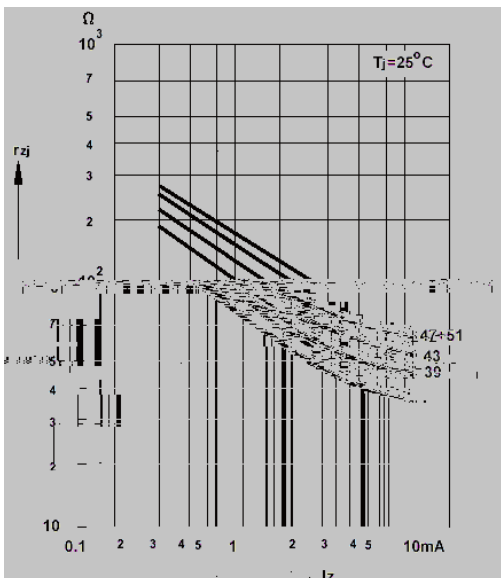
Capacitance versus Zener voltage



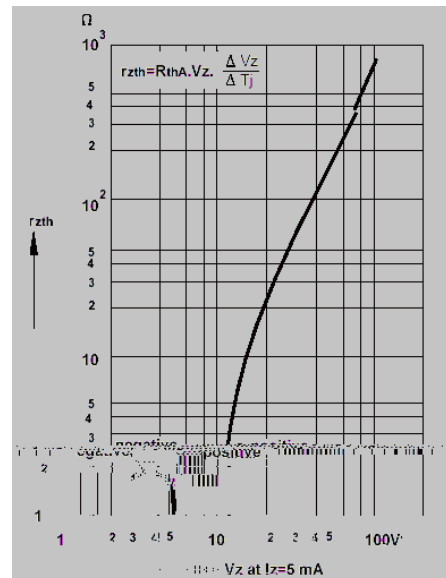
Dynamic resistance versus Zener current



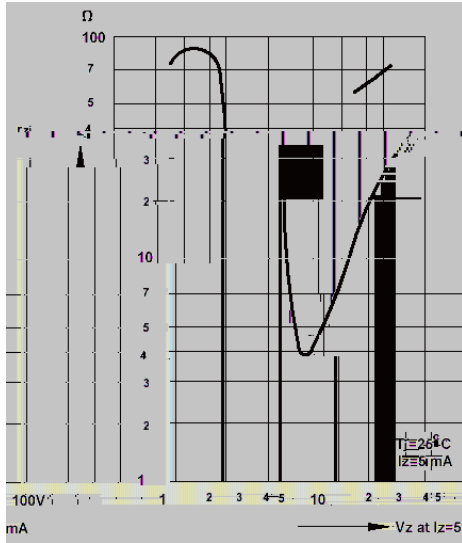
Dynamic resistance versus Zener current



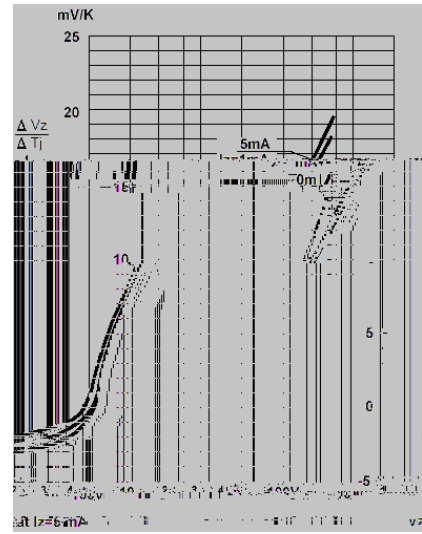
Thermal differential resistance versus Zener voltage



Dynamic resistance versus Zener voltage



Temperature dependence of Zener voltage versus Zener voltage



Temperature dependence of Zener voltage versus Zener voltage

Change of Zener voltage versus junction temperature

